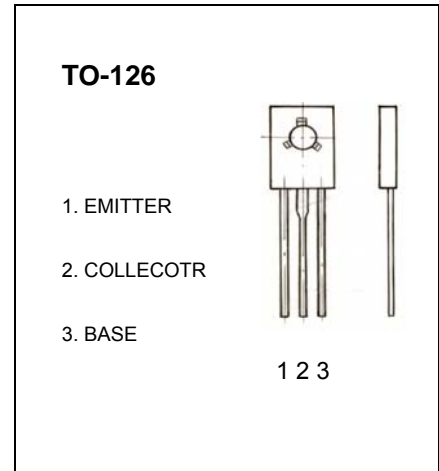


# 深圳市晶泰源电子有限公司

## 2SC1162 TRANSISTOR (NPN)

### FEATURES

Low frequency power amplifier



### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Emitter Voltage	35	V
$V_{CEO}$	Collector-Emitter Voltage	35	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	2.5	A
$P_C$	Collector Power Dissipation	0.75	W
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35\text{V}, I_E=0$			20	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			20	$\mu\text{A}$
DC current gain	$h_{FE1}$	$V_{CE}=2\text{V}, I_C=0.5\text{A}$	60		320	
	$h_{FE2}$	$V_{CE}=2\text{V}, I_C=1.5\text{A}^*$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=200\text{mA}$			1	V
Base-collector voltage	$V_{BE}$	$V_{CE}=2\text{V}, I_C=1.5\text{A}$			1.5	V
Transition frequency	$f_T$	$V_{CE}=2\text{V}, I_C=200\text{mA}$		180		MHz

\* pulse test

### CLASSIFICATION OF $h_{FE1}$

Rank	B	C	D
Range	60-120	100-200	160-320